

# **Poster WEPFDV004** A New Model for Q-slope in SRF Cavities: RF Heating at Multiple Josephson Junctions at Weakly Linked Grain Boundaries or Dislocations

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### Abstract

Several models are already proposed for Q-slopes in SRF cavity performance, medium field Q-slope (MFQS), high field Q-slope (HFQS). However, these does not explain both in a way unified. Here, a new model by multiple Josephson junctions at weakly linked grain boundaries or dislocations is proposed for the unified explanation. This model suggests two kind of junctions: ceramic like one and weak superconductor one. If plotted the field vs. RF power dissipation, an increase of RF loss is remarkably observed in proportional to the cube of fields, on both BCP'ed and EP'ed cavity (MFQS). An exponential RF dissipation is often observed at high fields for BCP'ed cavity (HFQS). If supposed the number of J-junctions linearly increases with the fields (this is explained by the flux quantum penetration condition), these behaviors are easily explained. In addition, this model has a potential to explain the anti-Q slope behavior observed in Nitrogen doped or midtemperature baked cavity. In this paper, this model will be explained, then several data analysis results will be presented.

### Motivation: FRIB cavity data analysis

- HFQS is well fitted by FN (Flower Nordheim)-plot (FE), which suggests *a tunneling mechanism* as behind physics.
- Ep<sup>3</sup> dependence commonly observed in Ploss vs Ep
- Example: 85-029 0.085QWR



RF

example: SRTiO<sub>3</sub>

**Bicrystal grain boundary** 

### Data analysis example by this model

Assume **NO thermal feedback for 2K data**, because L-He has no bubbling below  $\lambda$ -point (2.17K) ) Plotting Ep vs Ploss is easy to data analysis, linear combination of RF dissipation mechanisms 2) BCS heating (due to BCS + residual surface resistance) is data fitted by α x Ep<sup>2</sup>

- $\alpha$  is obtained by a couple of lowest field data, and Ploss = 0 at Ep=0
- Medium field region ( $C_2 < Ep < C_4$ ) is data fitted by:
  - BCS heating + *J*-heating (Ep<sup>3</sup> term) =  $\alpha \times Ep^2 + C_1 \times (Ep C_2)^2 \times E_P$
  - C<sub>2</sub>: onset of the J-heating
- High field region ( $Ep > C_4$ ) is data fitted by BCS heating + J-heating +HFQS 4) heating
- HFQS heating =  $C_3 \times (Ep C_4)^2 \times Ep \times exp[C_5 \times (Ep C_4) \times \beta]$



• C<sub>4</sub> is the HFQS onset, which is estimated by the Ploss vs Ep plot (right graph)

### • $\beta = [Bp/Ep] [T/(MV/m)]$





#### Josephson mechanism

- B. D. Josephson (1962). "Possible new effects in superconductive tunneling". Phys. Lett. 1 (7): 251–253
- Tunneling effect of Cooper pairs or Quasi-electrons through an insulator sandwiched by superconductors



- $I < I_{c}$ , Zero voltage due to tunneling of Cooper pairs, no electric resistance (RF emission)
- Josephson equations

1) 
$$I = I_C \sin(\varphi)$$
, 2)  $V(t) = \frac{\hbar}{2e} \cdot \frac{\partial \varphi}{\partial t}$ 

When applied V(t): V(t) = V<sub>0</sub> sin(
$$\omega$$
t) to Cooper pair chage,  
I(t) = I<sub>C</sub> sin (V<sub>0</sub> $\int_0^t sin(\omega t) dt$ )

is generated without any loss.

RF emission will happen, which has been already observed.

- $I > I_{c}$ , Quasi-electron makes tunneling the insulator, and produces voltage with electric resistance (RF dissipation) Substrate
- B. Bonin and H. Safa, Sacly, France, in 1991 proposed Josephson array model with RF dissipation by the analogy of HTC. "Power





Characteristics of current vs voltage at 4.2 K with Bicrystal grain boundary Josephson element at h= 2K Qo\* is nicely reproduced.

- Ploss =  $9.6817E-4 \times Ep^2 + 8.8864E-6 \times (Ep 2.0572)^2 \times Ep + 4.589E-7 \times (Ep 27.83)^2 \times Ep \times Ploss = 9.6817E-4 \times Ep^2 + 8.8864E-6 \times (Ep 2.0572)^2 \times Ep + 4.589E-7 \times (Ep 27.83)^2 \times Ep \times Ploss = 9.6817E-4 \times Ep^2 + 8.8864E-6 \times (Ep 2.0572)^2 \times Ep + 4.589E-7 \times (Ep 27.83)^2 \times Ep \times Ploss = 9.6817E-4 \times Ep^2 + 8.8864E-6 \times (Ep 2.0572)^2 \times Ep + 4.589E-7 \times (Ep 27.83)^2 \times Ep \times Ploss = 9.6817E-4 \times Ep^2 + 8.8864E-6 \times (Ep 2.0572)^2 \times Ep + 4.589E-7 \times (Ep 27.83)^2 \times Ep \times Ploss = 9.6817E-6 \times (Ep 2.0572)^2 \times Ep \times Plos = 9.6817E-6 \times (Ep 2.0572)^2 \times Ep \times Plos = 9.6817E-7 \times (Ep 27.83)^2 \times (Ep 27.83)$ exp [79.997 (Ep - 27.83) x1.7907E-3]
- 4.3 K Data analysis
- *Thermal Feedback* has a rather big impact on the Ploss
- This effect is estimated as: multiply  $C_6 \times Ep^2 \times P_{loss}$  on the RF dissipation

Eacc [MV/m]

- **P**loss =  $(1 + C_6 \times Ep^2) \times (BCS heating + J-Heating)$
- $=(1+1.2175E-3 \times Ep^2) \times (1.11538E-2 \times Ep^2 + 3.2124E-5 \times (Ep 1.250)^2 \times Ep)$
- BCS and thermal feedback are dominant, J-heating is hindered.



### Analysis of BCP'ed baked cavity

- LTB pushes up the J-heating/HFQS onsets, makes a smaller element size, and reduces both contribution at 4.3K.
- The smaller size can be produced by Oxygen diffusion during LTB.
- On the other hand, at 2K, both heating have a already small contribution by one order of magnitude, and the impact is not so remarkable as 4.3 K

Insulator size	Тетр	Unbaked	Baked
W [μm]	4.3 K	7.7	1.6
	2 K	8.2	1.7









case.